



NGTG20N60L2TF1G

N-Channel IGBT

600V, 20A, $V_{CE(sat)}$;1.45V Single TO-3PF-3L

ON Semiconductor®

<http://onsemi.com>

Features

- IGBT $V_{CE(sat)}$ =1.45V typ. (I_C =20A, V_{GE} =15V)
- IGBT t_f =67ns typ.
- Enhancement type
- Adaption of full isolation type package
- Maximum junction temperature T_j =175°C

Applications

- Power factor correction of white goods appliance
- General purpose inverter

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$, Unless otherwise specified

Parameter	Symbol	Conditions	Ratings	Unit	
Collector to Emitter Voltage	V_{CES}		600	V	
Gate to Emitter Voltage	V_{GES}		± 20	V	
Collector Current (DC)	I_C *1	Limited by T_{jmax}	@ $T_c=25^\circ\text{C}$ *2	40	A
			@ $T_c=100^\circ\text{C}$ *2	20	A
Collector Current (Pulse)	I_{CP}	Pulse width Limited by T_{jmax}	105	A	
Allowable Power Dissipation	P_D	$T_c=25^\circ\text{C}$ (Our ideal heat dissipation condition) *2	64	W	
Junction Temperature	T_j		175	°C	
Storage Temperature	T_{stg}		-55 to +175	°C	

Note : *1 Collector Current is calculated from the following formula.

$$I_C(T_c) = \frac{T_{jmax} - T_c}{R_{th(j-c)} \times V_{CE(sat)}(T_j, I_C(T_c))}$$

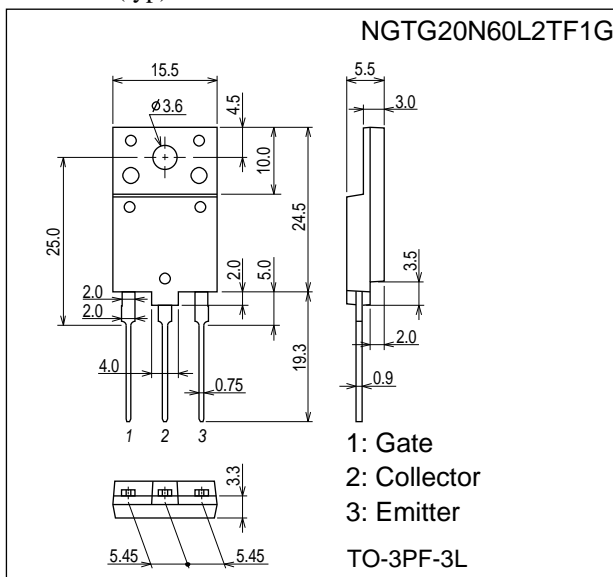
*2 Our condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

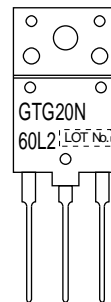
unit : mm (typ) 7538-001



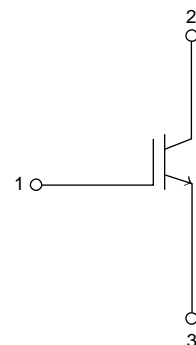
Ordering & Package Information

Device	Package	Shipping	note
NGTG20N60L2TF1G	TO-3PF-3L SC-94	30 pcs. / tube	Pb-Free

Marking



Electrical Connection



NGTG20N60L2TF1G

Electrical Characteristics at Ta = 25°C, Unless otherwise specified

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector to Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=500\mu A, V_{GE}=0V$	600			V
Collector to Emitter Cut off Current	I_{CES}	$V_{CE}=600V, V_{GE}=0V$	$T_c=25^\circ C$		10	μA
			$T_c=150^\circ C$		1	mA
Gate to Emitter Leakage Current	I_{GES}	$V_{GE}=\pm 20V, V_{CE}=0V$			± 100	nA
Gate to Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE}=20V, I_C=250\mu A$	4.5		6.5	V
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=20A$	$T_c=25^\circ C$	1.45	1.65	V
			$T_c=150^\circ C$	1.8		V
Input Capacitance	C_{ies}	$V_{CE}=20V, f=1MHz$		2000		pF
Output Capacitance	C_{oes}			60		pF
Reverse Transfer Capacitance	C_{res}			50		pF
Turn-ON Delay Time	$t_{d(on)}$			60		ns
Rise Time	t_r	$V_{CC}=300V, I_C=20A$ $R_G=30\Omega, L=200\mu H$		37		ns
Turn-ON Time	t_{on}			400		ns
Turn-OFF Delay Time	$t_{d(off)}$	$V_{GE}=0V/15V$ $V_{clamp}=400V$		193		ns
Fall Time	t_f		See Fig.1, See Fig.2		67	
Turn-OFF Time	t_{off}			281		ns
Total Gate Charge	Q_g	$V_{CE}=300V, V_{GE}=15V, I_C=20A$		84		nC
Gate to Emitter Charge	Q_{ge}			16		nC
Gate to Collector "Miller" Charge	Q_{gc}			37		nC

Thermal Characteristics at Ta = 25°C, Unless otherwise specified

Parameter	Symbol	Conditions	Ratings	Unit
Thermal Resistance (junction- Case)	$R_{th(j-c)}$	$T_c=25^\circ C$ (our ideal heat dissipation condition)*2	2.33	$^\circ C/W$
Thermal Resistance (junction- atmosphere)	$R_{th(j-a)}$		47.5	$^\circ C/W$

Fig.1 Switching Time Test Circuit

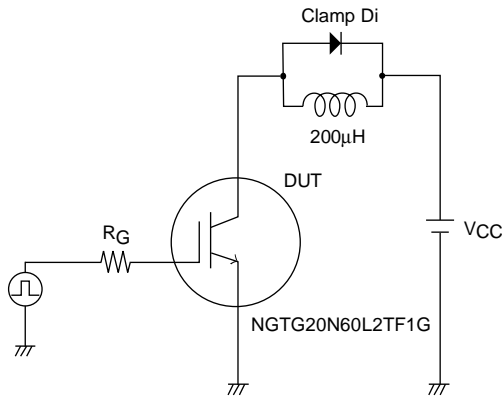
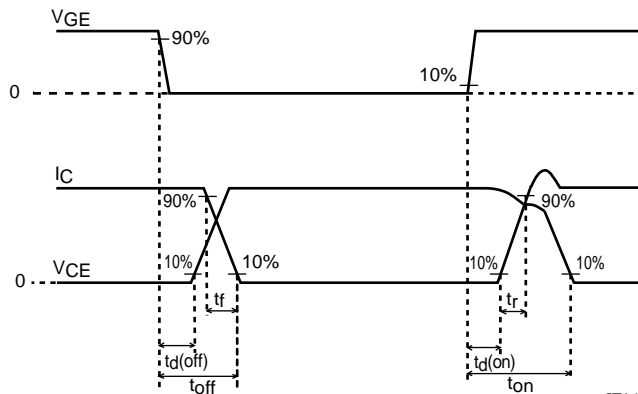
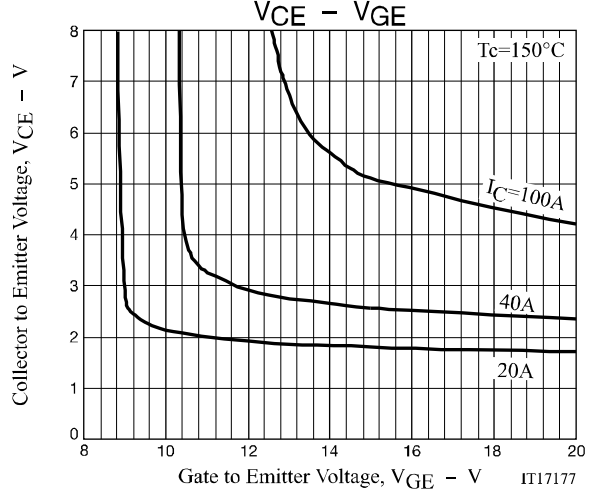
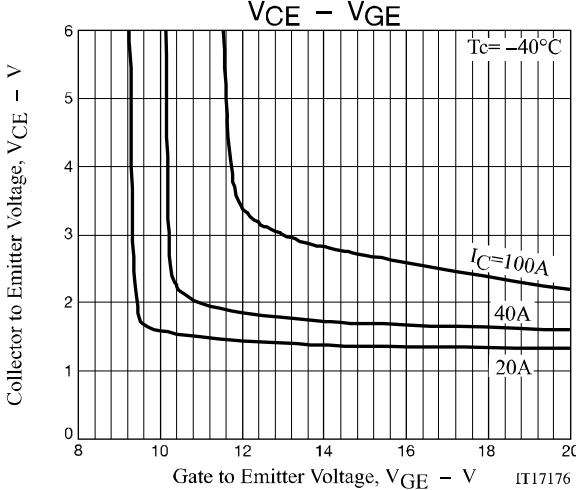
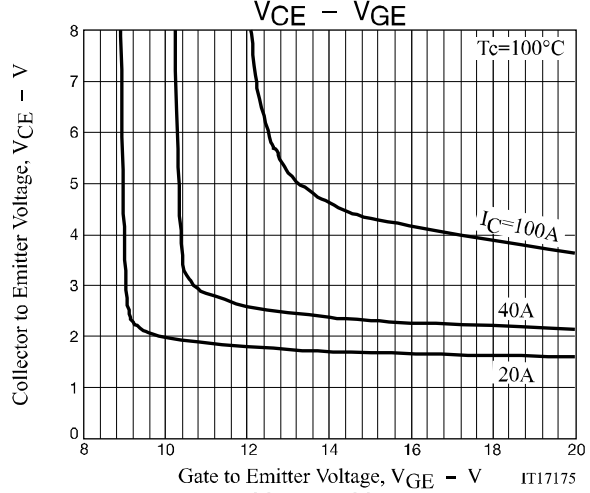
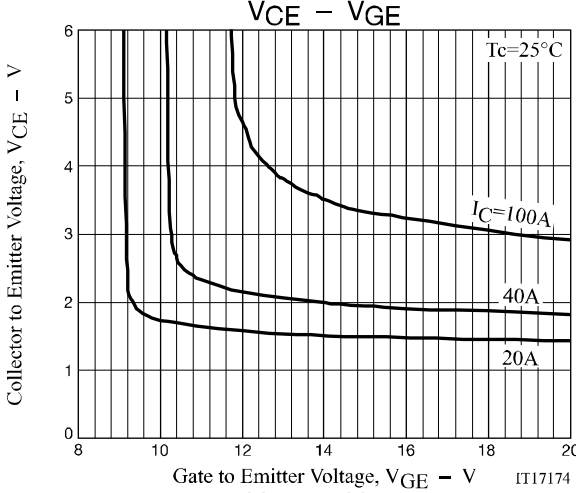
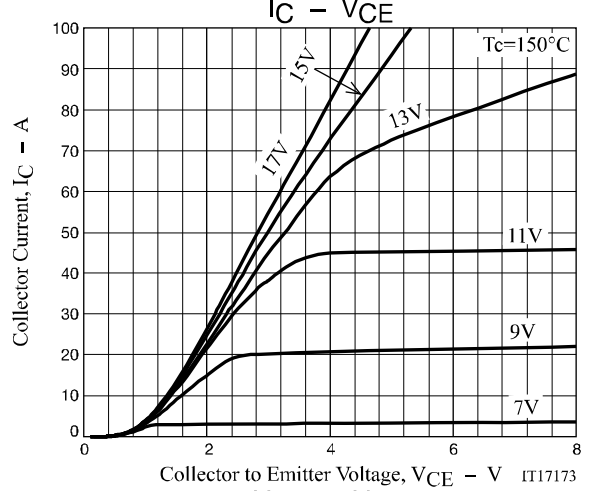
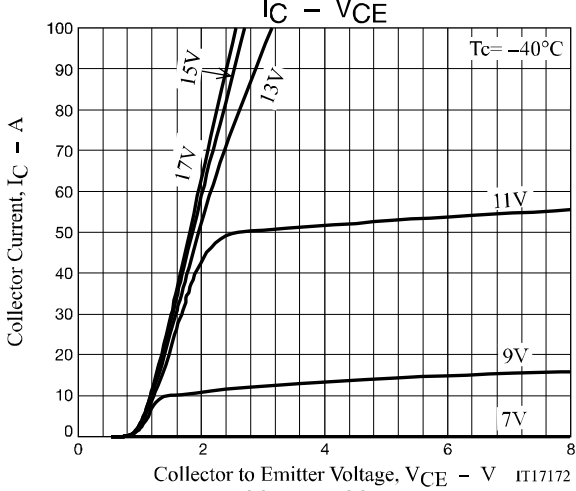
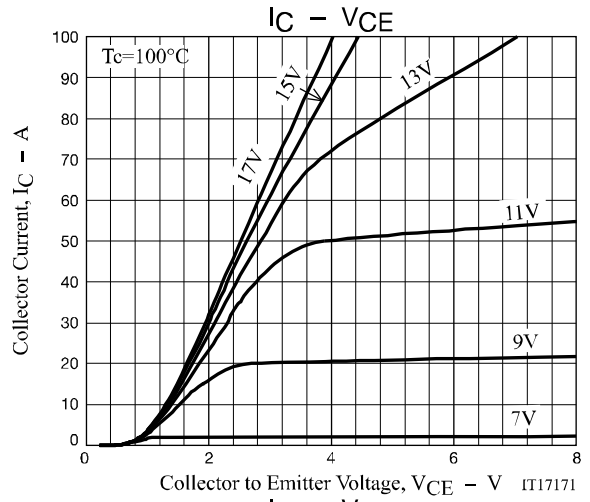
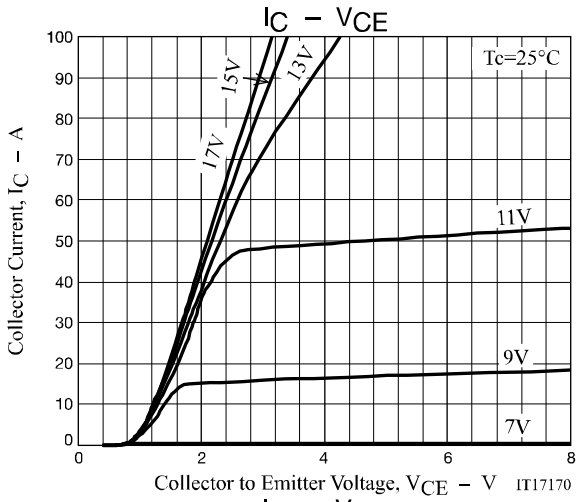


Fig.2 Timing Chart

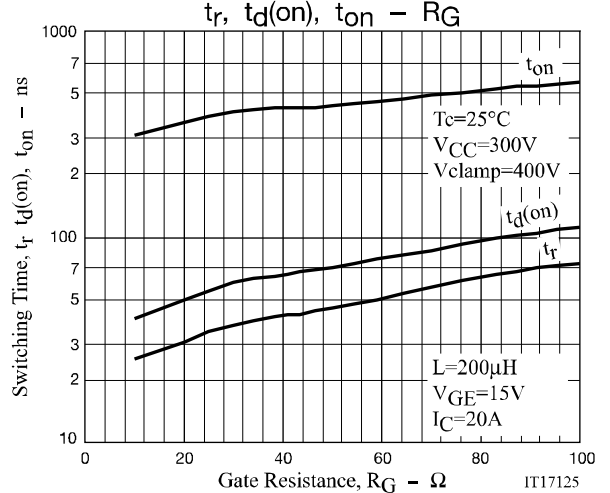
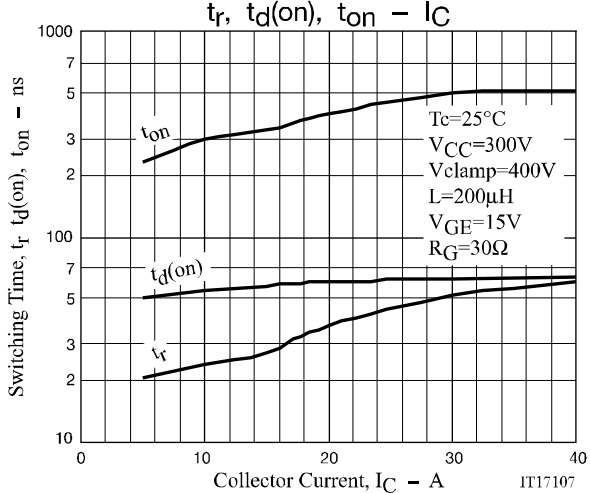
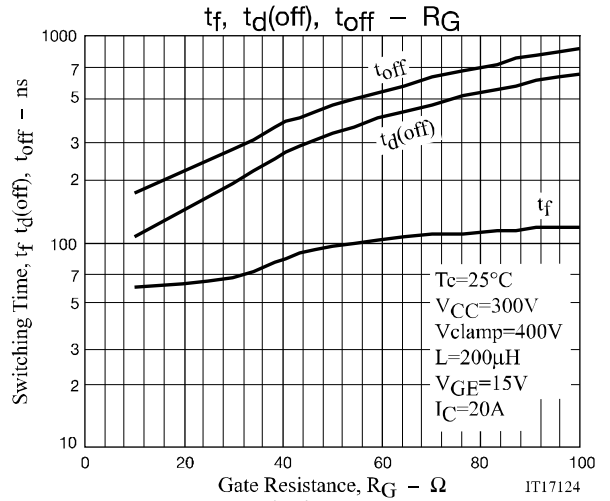
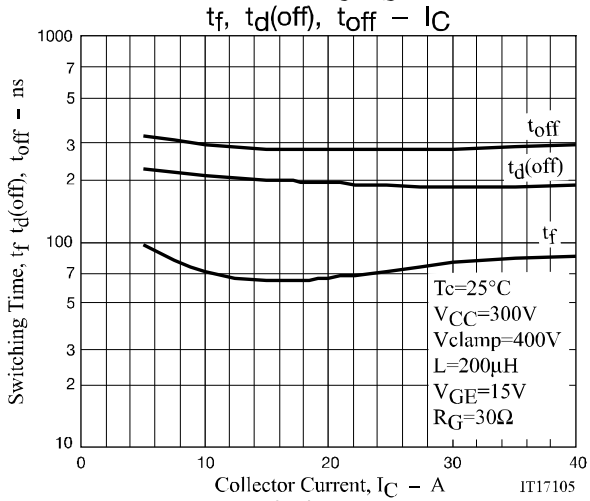
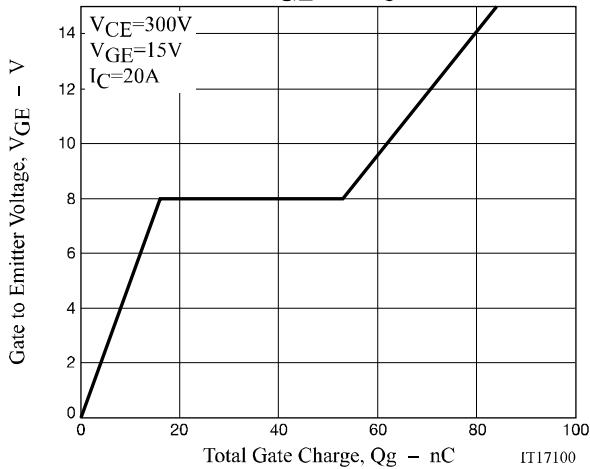
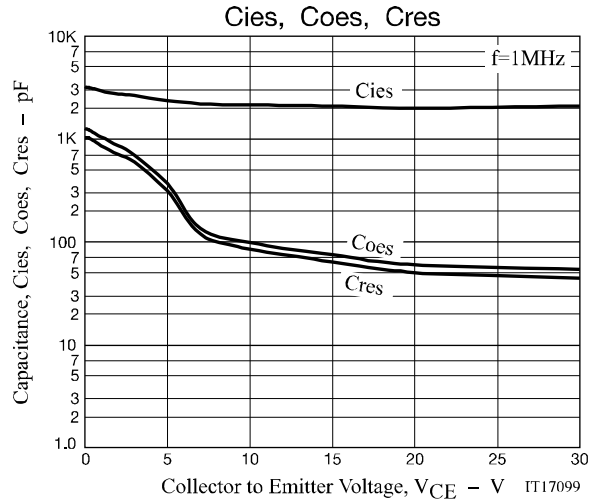
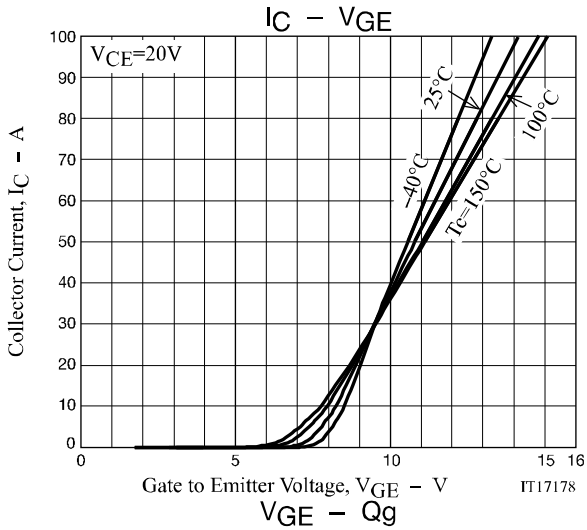


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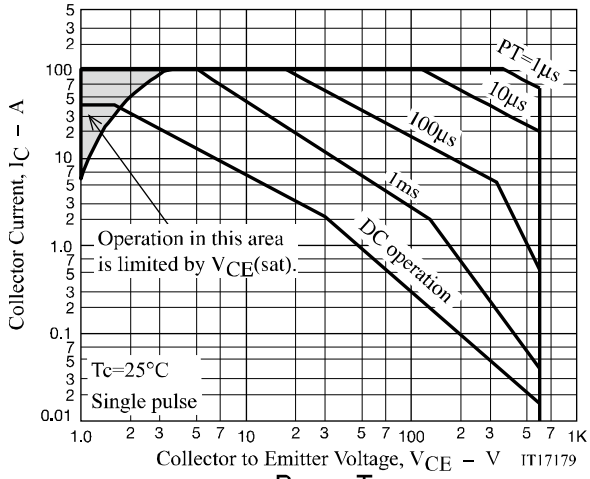


NGTG20N60L2TF1G

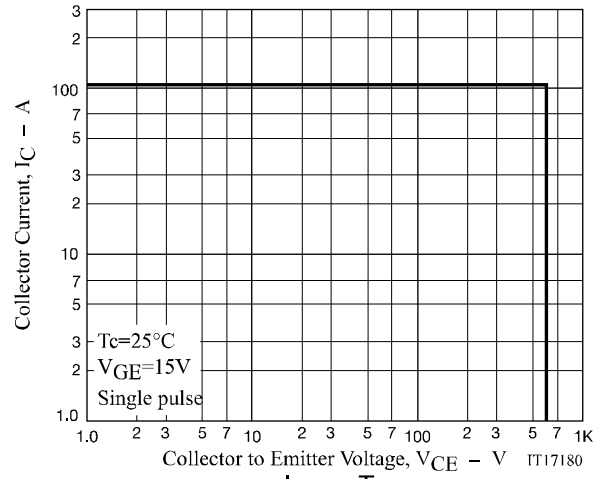


NGTG20N60L2TF1G

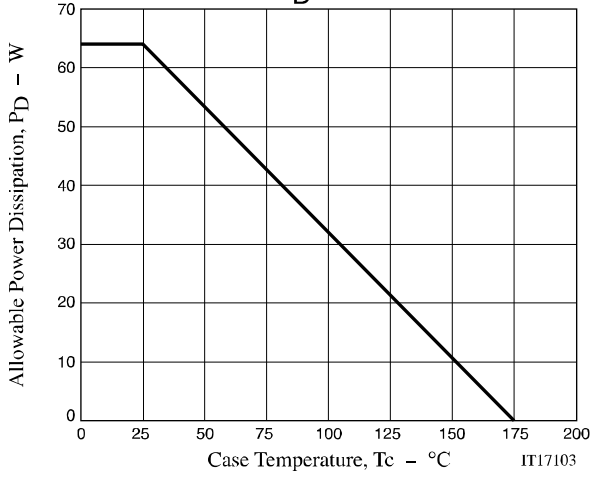
Forward Bias A S O



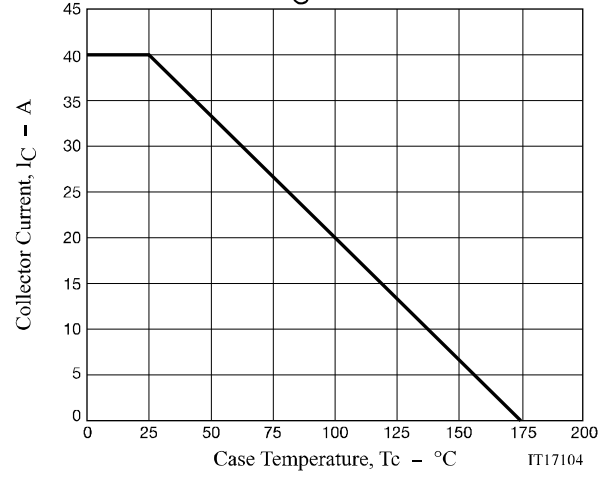
Reverse Bias A S O



$P_D - T_c$



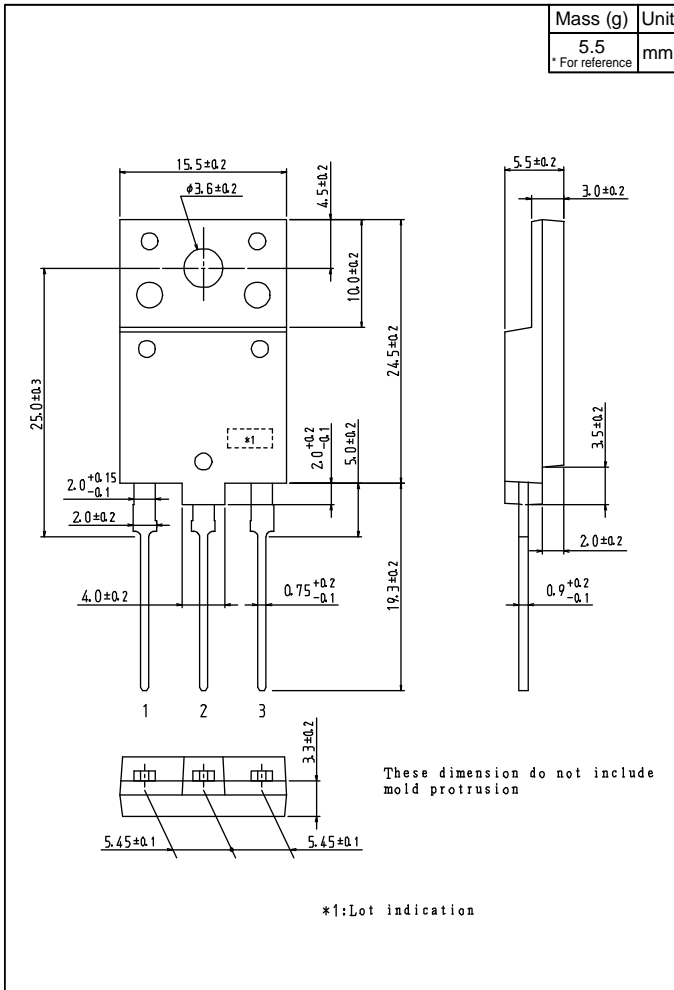
$I_C - T_c$



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Outline Drawing

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